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(71) Applicants: **APPLIED MATERIALS, INC.** [US/US];

3050 Bowers Avenue, Santa Clara, CA 95054 (US).

NATIONAL UNIVERSITY OF SINGAPORE [SG/SG];

21 Lower Kent Ridge Road, Singapore 119077 (SG).

(72) Inventors: **LEONCINI, Andrea**; Applied Materials Singa-

pore Technology PTE LTD, 10 Science Park Road,

#02-03, The Alpha Science Park II, Singapore 117684

(SG). **MEHLMANN, Paul**; National University of Singa-

pore, 21 Lower Kent Ridge Road, Singapore 119077

(SG). **DORDEVIC, Nemanja**; National University of Singa-

pore, 21 Lower Kent Ridge Road, Singapore 119077

(SG). **HUYNH, Han, Vinh**; National University of Singa-

pore, 21 Lower Kent Ridge Road, Singapore 119077 (SG).

YONG, Doreen, Wei, Ying; Applied Materials Singapore

Technology PTE LTD, 10 Science Park Road, #02-03, The

Alpha Science Park II, Singapore 117684 (SG).

(74) Agent: **SMIRK, Rebecca, A.**; Servilla Whitney LLC, 33

Wood Avenue South, Suite 830, Iselin, NJ 08830 (US).

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(54) Title: MOLYBDENUM(IV) AND MOLYBDENUM(III) PRECURSORS FOR DEPOSITION OF MOLYBDENUM FILMS

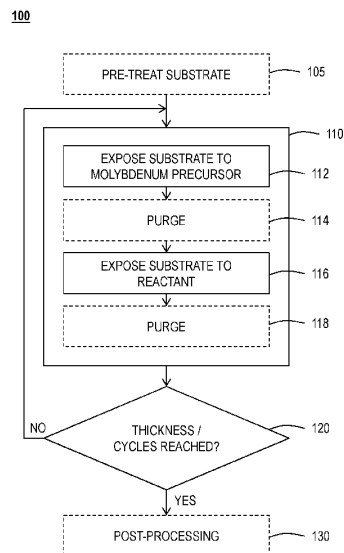


FIG. 1

(57) Abstract: Molybdenum(IV) and molybdenum(III) coordination complexes are described. Methods for depositing molybdenum-containing films on a substrate are described. The substrate is exposed to a molybdenum precursor and a reactant to form the molybdenum-containing film (e.g., elemental molybdenum, molybdenum oxide, molybdenum carbide, molybdenum silicide, molybdenum nitride). The exposures can be sequential or simultaneous.

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